

ABSTRACT OF THE DISCLOSURE

A thin-film transistor includes: a pair of n-type heavily doped regions that are horizontally spaced apart from each other; p-type channel regions that are located between the n-type heavily doped regions so as to face their associated gate electrodes, respectively; an n-type intermediate region provided between two adjacent ones of the channel regions; and two pairs of lightly doped regions. The lightly doped regions in one of the two pairs have mutually different carrier concentrations and are located between one of the heavily doped regions and one of the channel regions that is closer to the heavily doped region than any other channel region is. The lightly doped regions in the other pair also have mutually different carrier concentrations and are located between the other heavily doped region and another one of the channel regions that is closer to the heavily doped region than any other channel region is.

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